Contributors

Hermann A. Haus (S'50–A'55–SM'58–F'62) was born in Ljubljana, Yugoslavia, in 1925. He received the B.S. degree from Union College, Schenectady, N.Y., in 1949, the M.S. degree from Rensselaer Polytechnic Institute, Troy, N. Y., in 1951, and the Sc.D. degree from the Massachusetts Institute of Technology, Cambridge, in 1954.

He is engaged in research in electromagnetic theory and lasers at the Research Laboratory of Electronics, and is Professor of Electrical Engineering, both at the Massachusetts Institute of Technology. He was a Guggenheim Fellow in 1959–1960. He was on the Editorial Board of the *Journal of Applied Physics* for the term 1960 to 1963 and is at present on the Editorial Board of *Electronics Letters*.

Dr. Haus is a member of Sigma Xi and the American Physical Society.

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Kaneyuki Kurokawa (M'60) was born in Tokyo, Japan, on August 14, 1928. He received the B.S. and Ph.D. degrees in electrical engineering from the University of Tokyo, Tokyo, Japan, in 1951 and 1958, respectively.

In 1957 he became an Assistant Professor at the University of Tokyo. From 1960 to 1961 he was on leave of absence from the University to Bell Telephone Laboratories, Inc., Murray Hill, N. J. In 1963 he returned to Bell Laboratories where he currently supervises a group responsible for millimeter-wave subsystem developments.

Dr. Kurokawa is a member of the Institute of Electronics and Communication Engineers of Japan.

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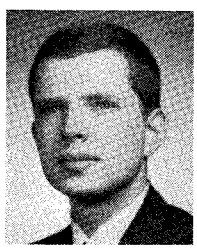

William H. Leighton, Jr. (S'63–M'69) was born in Christiana, Pa., on March 7, 1943. He received the B.S. degree in electrical engineering from Lehigh University, Bethlehem, Pa., in 1965, and the M.S. and Ph.D. degrees in electrical engineering from Carnegie-Mellon University, Pittsburgh, Pa., in 1966 and 1971, respectively.

Since 1970 he has been engaged in research on ferroelectric devices at Sandia Laboratories, Albuquerque, N. Mex.

Dr. Leighton is a member of Eta Kappa Nu and Tau Beta Pi.

Arthur G. Milnes (SM'55–F'68) was born in Heswall, England, on July 30, 1922. He received the B.S. degree in electrical engineering in 1943, and the M.S. and D.Sc. degrees in 1947 and 1956, respectively, all from the University of Bristol, Bristol, England.

From 1947 to 1950 he carried out research work at the University of Bristol on magnetic amplifiers and is the author of a book and research papers on this subject. From 1943 to 1957 he held Scientific Officer posts at the Royal Aircraft Establishment, Farnborough, England, apart from the academic year 1954–1955, which was spent on a Royal Society National Academy of Science Fellowship at Carnegie Institute of Technology, Pittsburgh, Pa. In 1957 he returned to C.I.T., now Carnegie-Mellon University, where he is Professor of Electrical Engineering with research interests in the semiconductor-device and solid-state fields. He is co-author of the forthcoming book *Heterojunctions and Metal-Semiconductor Junctions*.

Dr. Milnes is a member of the American Physical Society and the Electrochemical Society, and a Fellow of the Institution of Electrical Engineers (London).

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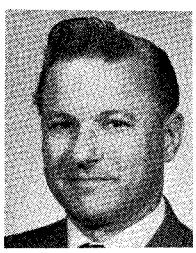

Robert A. Pucel (S'48–A'52–M'56–SM'64) was born on December 27, 1926. He received the B.S. and M.S. degrees in 1951, and the D.Sc. degree in 1955, in electrical communications, all from Massachusetts Institute of Technology, Cambridge.

From 1948 to 1951 he was a Test Engineer on the M.I.T. Cooperative Course with General Electric Company. Following his graduation he joined the Microwave Tube Group at the Research Division of Raytheon. A year later he returned to M.I.T. During the period 1952 to 1955 he was a Staff Member of the M.I.T. Research Laboratory of Electronics doing theoretical studies in electric network theory which were the basis for his doctoral dissertation. He rejoined the Raytheon Research Division in 1955. In 1966 he organized the Microwave Semiconductor and Integrated Circuits Program. Presently he is working on theoretical problems of microwave semiconductor devices, including transistors. His work has involved theoretical and experimental feasibility studies of new semiconductor device concepts and the design of high-frequency semiconductor devices, for example the spacistor, tunnel diode, varactor, avalanche diode, and Gunn and LSA structures. Recently his activities also have included theoretical and experimental studies of microstrip propagation on dielectric and ferrite substrates, thin film components for microwave integrated circuits, and microwave semiconductor devices. He has written numerous publications and internal reports on the above topics.

Dr. Pucel is a member of Sigma Xi, the Professional Technical Group on Electron Devices, and the Professional Technical Group on Microwave Theory and Techniques. Dr. Pucel is also a Registered Professional Engineer of the Commonwealth of Massachusetts.

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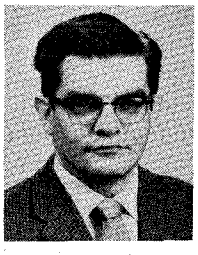

G. M. Royer (S'59–M'60) was born in Bassano, Alta., Canada, on November 12, 1933. He received the B.Sc.E.E. degree from the University of Alberta, Edmonton, Alta., Canada, in 1960, and the M.A.Sc. degree from the University of Toronto, Toronto, Ont., Canada, in 1964.

In 1960 and 1961 he was employed by the Department of Transport, Ottawa, Ont., Canada. In 1963 he joined the Defence Research Telecommunications Establishment (now a part of the Communications Research Center), Ottawa, where he has been involved in the measurement of radar cross section and microwave component research.

Hermann Statz received the Dipl. Phys. degree in 1949, and the Ph.D. degree in 1951, both in physics, from the Technische Hochschule, Stuttgart, Germany.

From 1949 to 1951 he was a Research Assistant at the Max Planck Institute of Metal Research in Stuttgart. On a fellowship he did postgraduate work at the Technische Hochschule from 1951 to 1952 in solid state physics. From 1952 to 1953 he was a Research Staff Member at M.I.T., Cambridge, Mass., working in the Solid State and Molecular Theory Group under Prof. J. C. Slater. In 1953 he joined the Research Division of Raytheon Company as Group Leader. In 1958 he became an Assistant Division Manager, and in 1969 he was named Technical Director and Assistant Division Manager of the Research Division. His work produced numerous publications in the fields of semiconductor surfaces, semiconductor devices, paramagnetic resonance, exchange interactions of magnetic ions, masers, and lasers.

Dr. Statz is a fellow of the American Physical Society and a member of the Board of Editors of the *Journal of Applied Physics* and *Applied Physics Letters*.